

April 1995

30A, 100V - 200V Ultrafast Dual Diodes**Features**

- Ultrafast with Soft Recovery <45ns
- Operating Temperature +175°C
- Reverse Voltage Up to 200V
- Avalanche Energy Rated
- Planar Construction

Applications

- Switching Power Supplies
- Power Switching Circuits
- General Purpose

Description

RURG3010CC, RURG3015CC and RURG3020CC (TA9645) are ultrafast dual diodes with soft recovery characteristics ($t_{RR} < 45\text{ns}$). They have low forward voltage drop and are silicon nitride passivated ion-implanted epitaxial planar construction.

These devices are intended for use as freewheeling/clamping diodes and rectifiers in a variety of switching power supplies and other power switching applications. Their low stored charge and ultrafast recovery with soft recovery characteristic minimizes ringing and electrical noise in many power switching circuits reducing power loss in the switching transistors.

PACKAGING AVAILABILITY

PART NUMBER	PACKAGE	BRAND
RURG3010CC	TO-247	RURG3010C
RURG3015CC	TO-247	RURG3015C
RURG3020CC	TO-247	RURG3020C

NOTE: When ordering, use the entire part number.

Absolute Maximum Ratings $T_C = +25^\circ\text{C}$

	RURG3010CC	RURG3015CC	RURG3020CC	UNITS
Peak Repetitive Reverse Voltage	V_{RRM}	100	150	V
Working Peak Reverse Voltage	V_{RWM}	100	150	V
DC Blocking Voltage	V_R	100	150	V
Average Rectified Forward Current (Per Leg)	$I_{F(AV)}$	30	30	A
($T_C = +145^\circ\text{C}$)				
Repetitive Peak Surge Current	I_{FSM}	70	70	A
(Square Wave, 20kHz)				
Nonrepetitive Peak Surge Current	I_{FSM}	325	325	A
(Halfwave, 1 Phase, 60Hz)				
Maximum Power Dissipation	P_D	125	125	W
Avalanche Energy	E_{AVL}	20	20	mJ
($L = 40\text{mH}$)				
Operating and Storage Temperature	T_{STG}, T_J	-65 to +175	-65 to +175	$^\circ\text{C}$

Specifications RURG3010CC, RURG3015CC, RURG3020CC

Electrical Specifications $T_C = +25^\circ\text{C}$, Unless Otherwise Specified

SYMBOL	TEST CONDITION	RURG3010CC LIMITS			RURG3015CC LIMITS			RURG3020CC LIMITS			UNITS
		MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
V_F	$I_F = 30\text{A}$	-	-	1.0	-	-	1.0	-	-	1.0	V
V_F	$I_F = 30\text{A}$ $T_C = +150^\circ\text{C}$	-	-	0.85	-	-	0.85	-	-	0.85	V
I_R	$V_R = 100\text{V}$	-	-	500	-	-	-	-	-	-	μA
	$V_R = 150\text{V}$	-	-	-	-	-	500	-	-	-	μA
	$V_R = 200\text{V}$	-	-	-	-	-	-	-	-	500	μA
I_R	$V_R = 100\text{V}$ $T_C = +150^\circ\text{C}$	-	-	100	-	-	-	-	-	-	mA
	$V_R = 150\text{V}$ $T_C = +150^\circ\text{C}$	-	-	-	-	-	100	-	-	-	mA
	$V_R = 200\text{V}$ $T_C = +150^\circ\text{C}$	-	-	-	-	-	-	-	-	1	mA
t_{RR}	$I_F = 1\text{A}$, $dI_F/dt = 100\text{A}/\mu\text{s}$	-	-	45	-	-	45	-	-	45	ns
t_{RR}	$I_F = 30\text{A}$, $dI_F/dt = 100\text{A}/\mu\text{s}$	-	-	50	-	-	50	-	-	50	ns
t_A	$I_F = 30\text{A}$, $dI_F/dt = 100\text{A}/\mu\text{s}$	-	20	-	-	20	-	-	20	-	ns
t_B	$I_F = 30\text{A}$, $dI_F/dt = 100\text{A}/\mu\text{s}$	-	15	-	-	15	-	-	15	-	ns
$R_{\theta JC}$		-	-	1.2	-	-	1.2	-	-	1.2	$^\circ\text{C}/\text{W}$

DEFINITIONS

V_F = Instantaneous forward voltage ($pw = 300\mu\text{s}$, $D = 2\%$).

I_R = Instantaneous reverse current.

t_{RR} = Reverse recovery time (See Figure 2), summation of $t_A + t_B$.

t_A = Time to reach peak reverse current (See Figure 2).

t_B = Time from peak I_{RM} to projected zero crossing of I_{RM} based on a straight line from peak I_{RM} through 25% of I_{RM} (See Figure 2).

$R_{\theta JC}$ = Thermal resistance junction to case.

E_{AVL} = Controlled avalanche energy (See Figures 7 and 8).

pw = pulse width.

D = duty cycle.

V_1 AMPLITUDE CONTROLS I_F
 V_2 AMPLITUDE CONTROLS dI_F/dt

L_1 = SELF INDUCTANCE OF

$R_4 + L_{\text{LOOP}}$

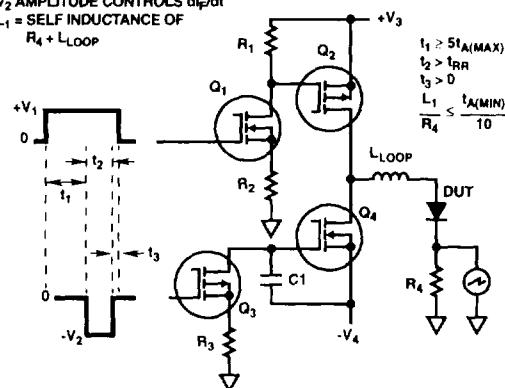


FIGURE 1. t_{RR} TEST CIRCUIT

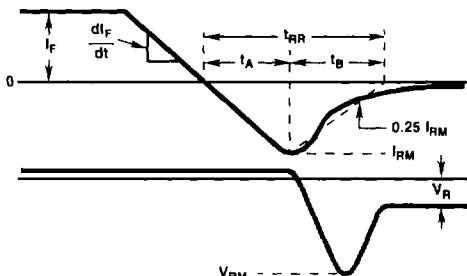
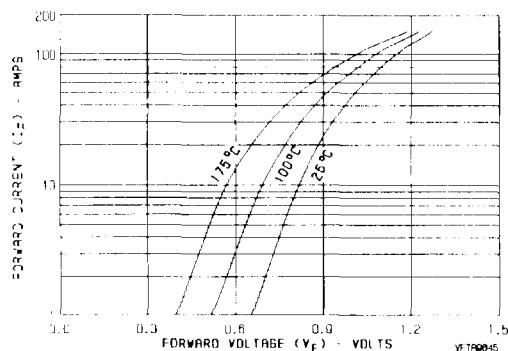
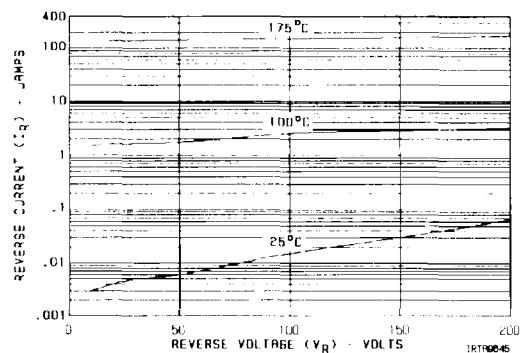
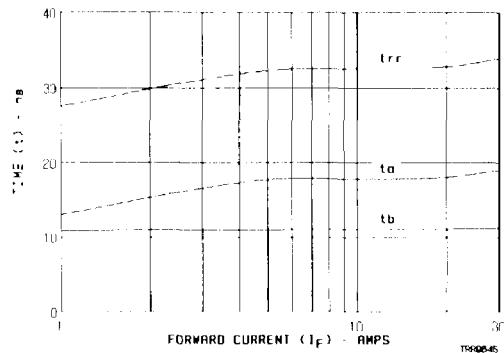
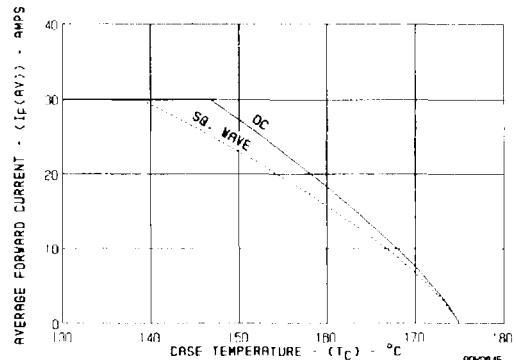
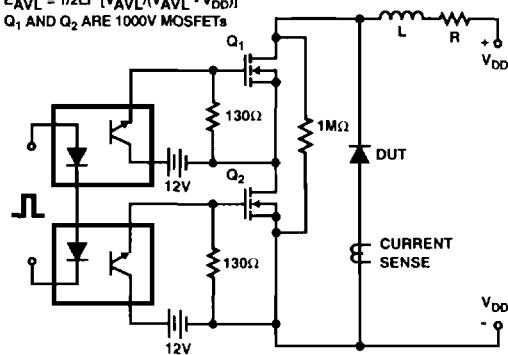
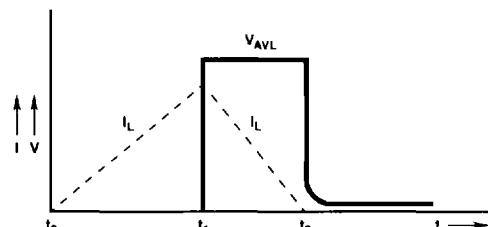


FIGURE 2. t_{RR} WAVEFORMS AND DEFINITIONS

RURG3010CC, RURG3015CC, RURG3020CC**Typical Performance Curves****FIGURE 3. TYPICAL FORWARD CURRENT vs FORWARD VOLTAGE DROP****FIGURE 4. TYPICAL REVERSE CURRENT vs VOLTAGE****FIGURE 5. TYPICAL t_{rr}, t_a AND t_b CURVES vs FORWARD CURRENT****FIGURE 6. CURRENT DERATING CURVE FOR ALL TYPES** $I_{MAX} = 1A$ $L \approx 40mH$ $R < 0.1\Omega$

$$E_{AVL} = 1/2L^2 [V_{AVL}/(V_{AVL} - V_{DD})]$$

Q₁ AND Q₂ ARE 1000V MOSFETs**FIGURE 7. AVALANCHE ENERGY TEST CIRCUIT****FIGURE 8. AVALANCHE CURRENT AND VOLTAGE WAVEFORMS**